

## CSM212P1DF1006-3

### 20V P-Channel Enhancement Mode MOSFET

**Voltage** -20 V **Current** -1000mA

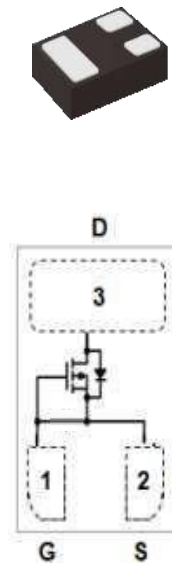
#### Features

- Advanced Trench Process Technology
- Specially Designed for Switch Load, PWM Application, etc.
- Green molding compound

#### Mechanical Data

- Case: DFN1006-3L Package
- Terminals : Solderable per MIL-STD-750, Method 2026
- Approx. Weight: 0.00002 ounces, 0.0007 grams

DFN1006-3L



### Maximum Ratings and Thermal Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS
Drain-Source Voltage		V <sub>DS</sub>	-20	V
Gate-Source Voltage		V <sub>GS</sub>	±12	
Continuous Drain Current (Note 4)		I <sub>D</sub>	-1000	mA
Pulsed Drain Current (Note 1)		I <sub>DM</sub>	-1500	
Power Dissipation	T <sub>a</sub> =25°C	P <sub>D</sub>	500	mW
	Derate above 25°C		4	mW/ °C
Operating Junction and Storage Temperature Range		T <sub>J</sub> ,T <sub>STG</sub>	-55~150	°C
Typical Thermal Resistance		R <sub>θJA</sub>	250	°C/W
- Junction to Ambient (Note 3,4)				

- Limited only By Maximum Junction Temperature

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### Electrical Characteristics ( $T_A=25^{\circ}\text{C}$ unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =-250uA	-20	-	-	V
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =-250uA	-0.3	-0.6	-1	
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-300mA	-	450	500	mΩ
		V <sub>GS</sub> =-2.5V, I <sub>D</sub> =-200mA	-	630	820	
		V <sub>GS</sub> =-1.8V, I <sub>D</sub> =-100mA	-	810	1200	
		V <sub>GS</sub> =-1.5V, I <sub>D</sub> =-100mA	-	1020	1600	
		V <sub>GS</sub> =-1.2V, I <sub>D</sub> =-100mA	-	1670	3000	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-20V, V <sub>GS</sub> =0V	-	-	-1	uA
Gate-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±12V, V <sub>DS</sub> =0V	-	-	±10	
Dynamic (Note 5)						
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =-10V, I <sub>D</sub> =-200mA, V <sub>GS</sub> =-4.5V (Note 2)	-	1.1	-	nC
Gate-Source Charge	Q <sub>gs</sub>		-	0.2	-	
Gate-Drain Charge	Q <sub>gd</sub>		-	0.1	-	
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =-10V, V <sub>GS</sub> =0V, f=1MHZ	-	51	-	pF
Output Capacitance	C <sub>oss</sub>		-	15	-	
Reverse Transfer Capacitance	C <sub>rss</sub>		-	2.2	-	
Turn-On Delay Time	td <sub>(on)</sub>	V <sub>DD</sub> =-10V, I <sub>D</sub> =-200mA, V <sub>GS</sub> =-4.5V, R <sub>G</sub> =6Ω (Note 2)	-	4.3	-	ns
Turn-On Rise Time	tr		-	20	-	
Turn-Off Delay Time	td <sub>(off)</sub>		-	33	-	
Turn-Off Fall Time	tf		-	25	-	
Drain-Source Diode						
Maximum Continuous Drain-Source Diode Forward Current	I <sub>S</sub>	---	-	-	-300	mA
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =-300mA, V <sub>GS</sub> =0V	-	-0.85	-1	V

#### NOTES:

1. Pulse width  $\leq 300\mu s$ , Duty cycle  $\leq 2\%$
2. Essentially independent of operating temperature typical characteristics.
3.  $R_{\theta JA}$  is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins mounted on a 1 inch FR-4 with 2oz. square pad of copper.
4. The maximum current rating is package limited.
5. Guaranteed by design, not subject to production testing.

## CSM212P1DF1006-3

### TYPICAL CHARACTERISTIC CURVES

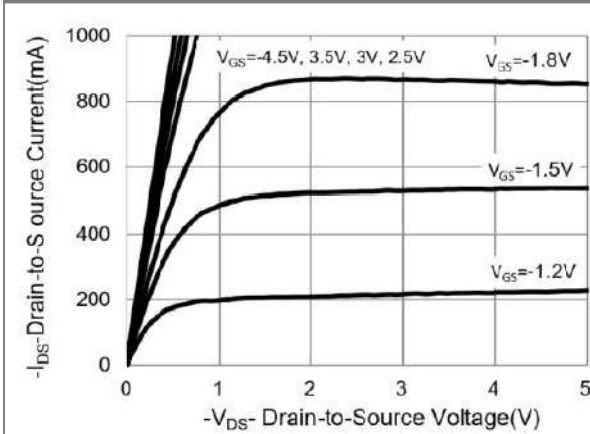


Fig.1 On-Region Characteristics

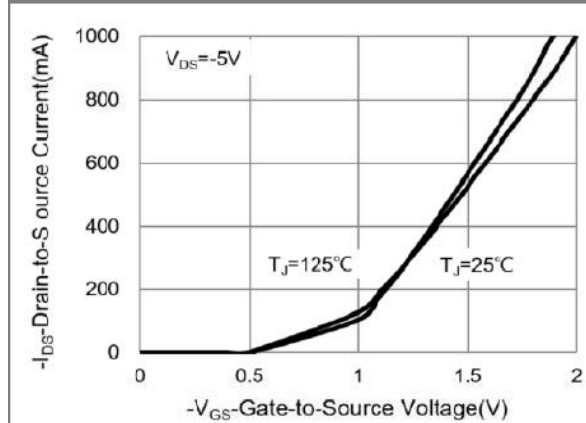


Fig.2 Transfer Characteristics

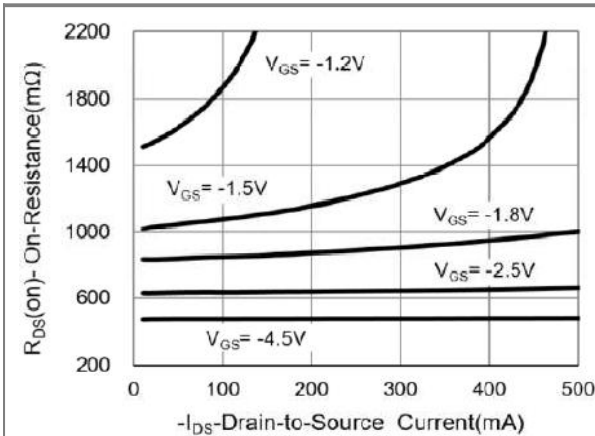


Fig.3 On-Resistance vs. Drain Current

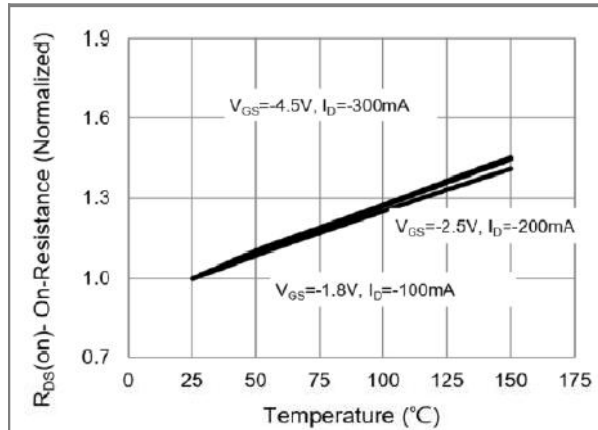


Fig.4 On-Resistance vs. Junction temperature

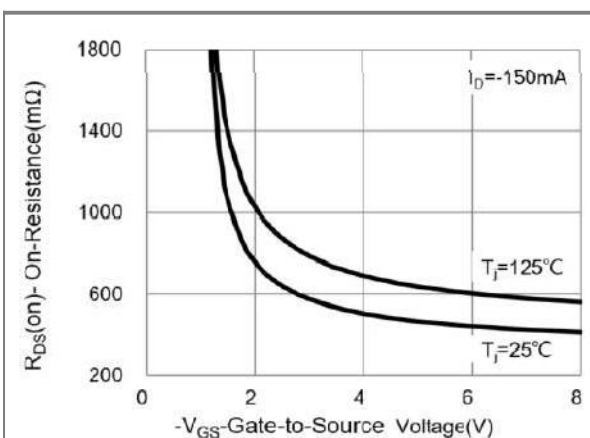


Fig.5 On-Resistance Variation with  $V_{GS}$

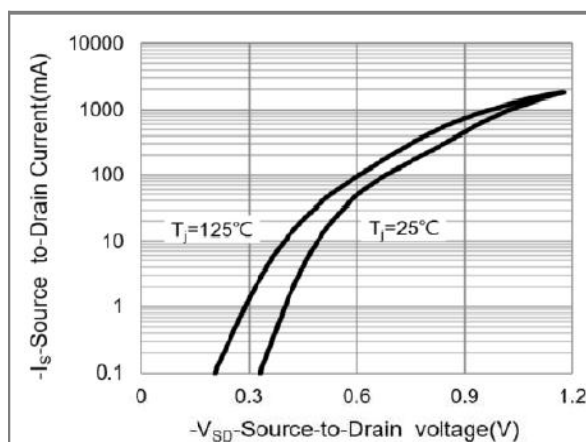


Fig.6 Body Diode Characteristics

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### TYPICAL CHARACTERISTIC CURVES

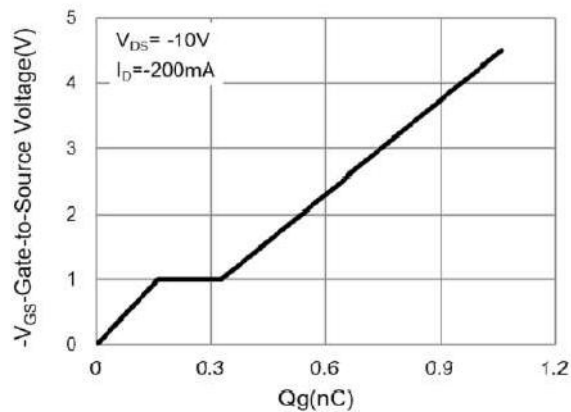


Fig.7 Gate-Charge Characteristics

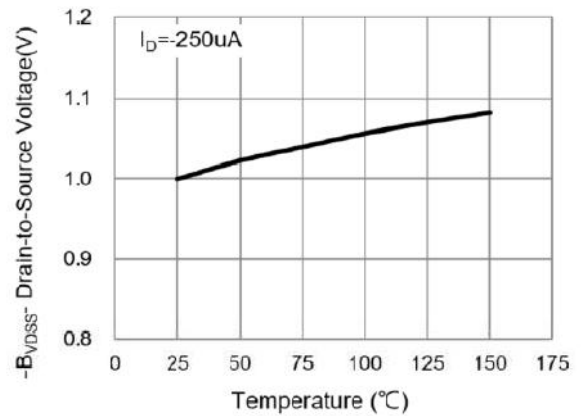


Fig.8 Breakdown Voltage Variation vs. Temperature

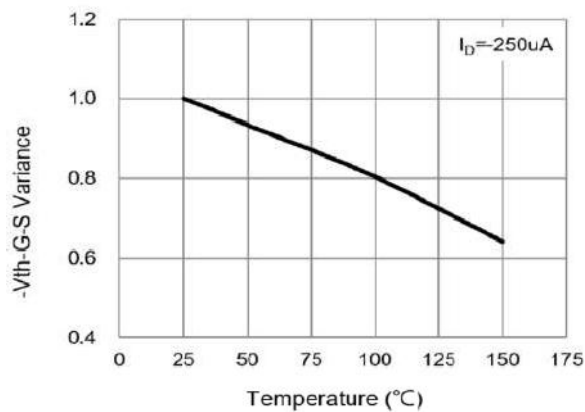


Fig.9 Threshold Voltage Variation with Temperature

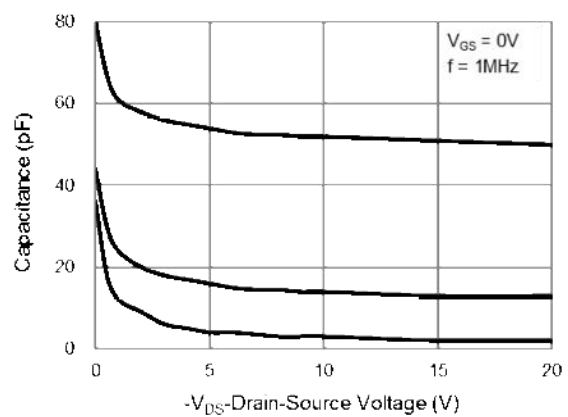


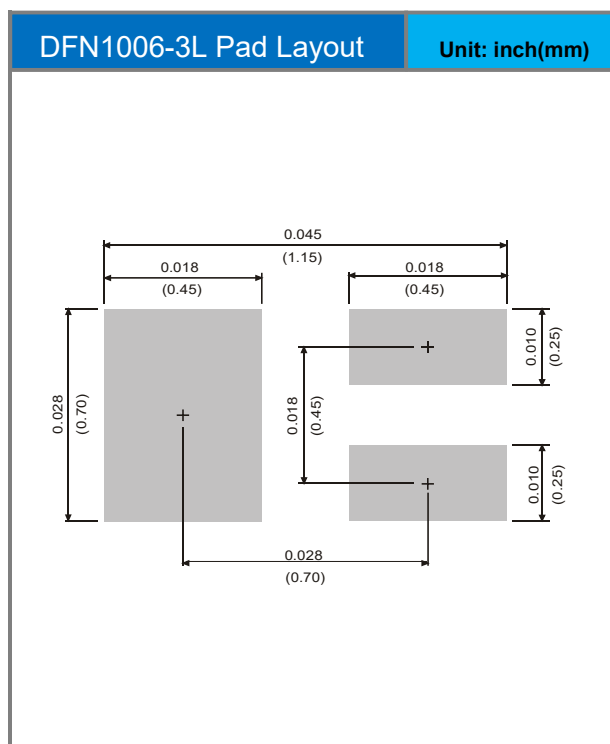
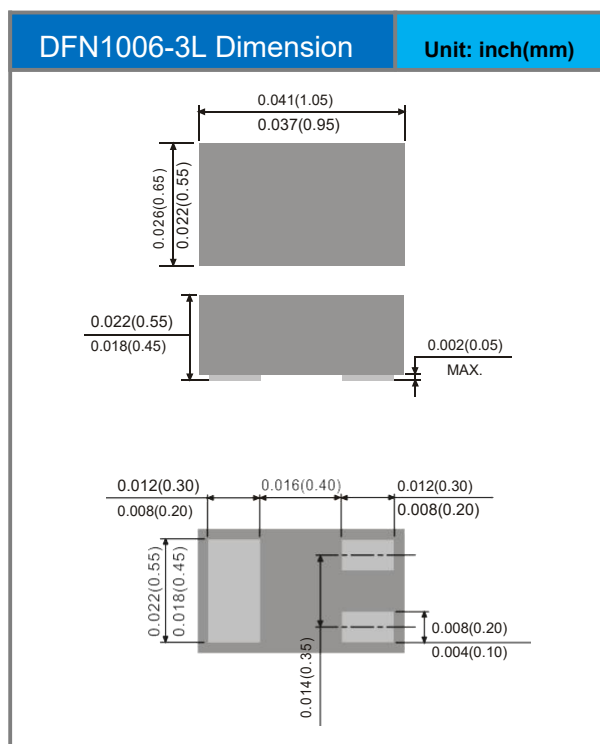
Fig.10 Capacitance vs. Drain-Source Voltage

## CSM212P1DF1006-3

### Part No Packing Code Version

Part No Packing Code	Package Type	Packing Type
CSM212P1DF1003-3	DFN1006-3L	10K / 7" Reel

### Packaging Information & Mounting Pad Layout



## **CSM212P1DF1006-3**

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